SSC8040GN4

N-Channel Enhancement Mode MOSFET

➢ Features

V_{DS}	V_{GS}	$R_{DS(ON)}$ Typ.	I_D
40V	±20V	21mΩ@10V	27A
		25mΩ@4V5	

➢ Description

This device is N-Channel enhancement MOSFET. Uses advanced trench technology and design to provide excellent RDSON with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit.

100% UIS + ΔVDS + Rg Tested!

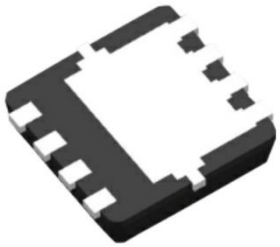
➢ Applications

- Motor Drive Control
- DCDC Conversion
- Power Supplies
- Synchronous Rectification

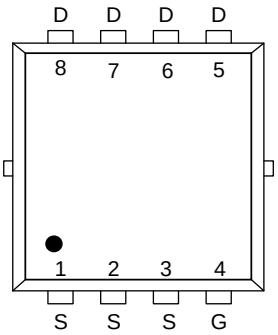
➢ Ordering Information

Device	Package	Shipping
SSC8040GN4	PDFN3.3X3.3-8L	5000/Reel

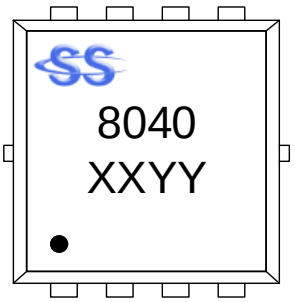
➢ Pin Configuration



PDFN3.3X3.3-8L (Bottom View)



Pin Configuration



Marking

(XXYY: Internal Traceability Code)

➢ Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V_{DSS}	Drain-to-Source Voltage		40	V
V_{GSS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current [d]	T_C=25℃	27	A
		T_C=100℃	14.7	
I_{DSM}	Continuous Drain Current [a]	T_A=25℃	9.8	A
		T_A=70℃	6.9	
I_{DM}	Pulsed Drain Current [b]		109	A
P_D	Power Dissipation [c]	T_C=25℃	25	W
		T_C=100℃	10	
P_{DSM}	Power Dissipation [a]	T_A=25℃	3.2	W
		T_A=70℃	2.05	
I_{AS}	Avalanche Current [b] L=0.5mH Single Pulse		8	A
E_{AS}	Avalanche Energy [b] L=0.5mH Single Pulse		16	mJ
T_J	Operation junction temperature		-55~150	℃
T_{STG}	Storage temperature range		-55~150	

➢ Thermal Resistance Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance [a]	39	℃/W
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	5	

Note:

a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz.copper, in a still air environment with T_A=25℃.The value in any given application depends on the user is specific board design. The power dissipation is based on the t≤10s thermal resistance rating.

b. Repetitive rating, pulse width limited by junction temperature.

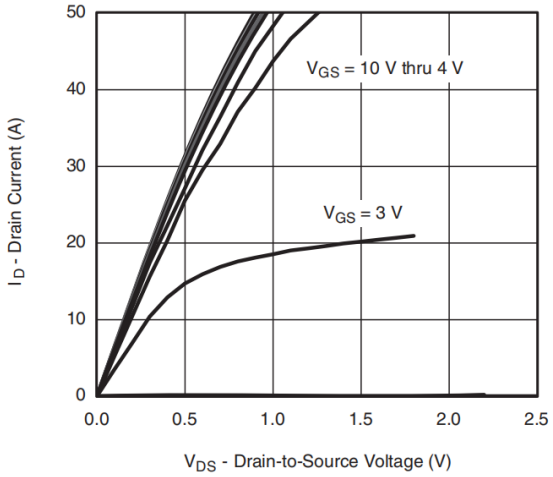
c. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

d. The maximum current rating is package limited.

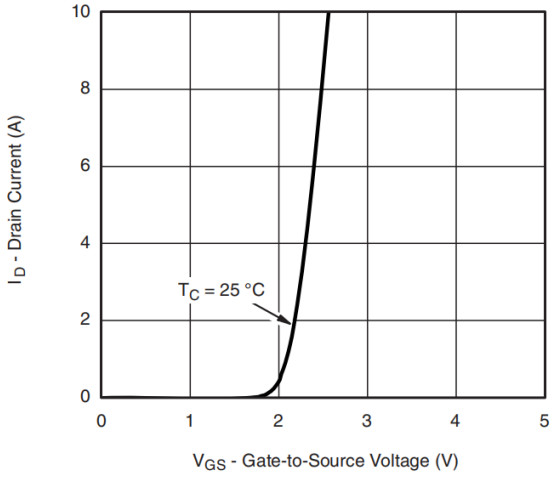
➢ Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250uA	40			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250uA	1	1.5	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 9A		21	27	mΩ
		V_{GS} = 4.5V, I_D = 6A		25	35	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40V, V_{GS} = 0V			1	uA
Gate-Source Leak Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
Transconductance	G_{FS}	V_{DS} = 5V, I_D = 6A		9.2		s
Forward Voltage	V_{SD}	V_{GS} = 0V, I_S = 6A		0.8	1.3	V
Input Capacitance	C_{ISS}	V_{DS} = 20V, V_{GS} = 0V, f = 1MHz		530		pF
Output Capacitance	C_{OSS}			68		
Reverse Transfer Capacitance	C_{RSS}			58		
Total Gate Charge	Q_G	V_{GS} = 10V, V_{DS} = 20V, I_D = 5A		13.5		nC
Gate to Source Charge	Q_{GS}			1.7		
Gate to Drain Charge	Q_{GD}			2.2		
Turn-on Delay Time	$T_{D(ON)}$	V_{GS} = 10V, V_{DS} = 20V, I_D = 5A, R_G = 3Ω		11		ns
Rise Time	T_r			9		
Turn-off Delay Time	$T_{D(OFF)}$			15		
Fall Time	T_f			10		
Diode Recovery Time	T_{rr}	I_F=10A, di/dt=100A/us		17		ns
Diode Recovery Charge	Q_{rr}	I_F=10A, di/dt=100A/us		8.5		nC

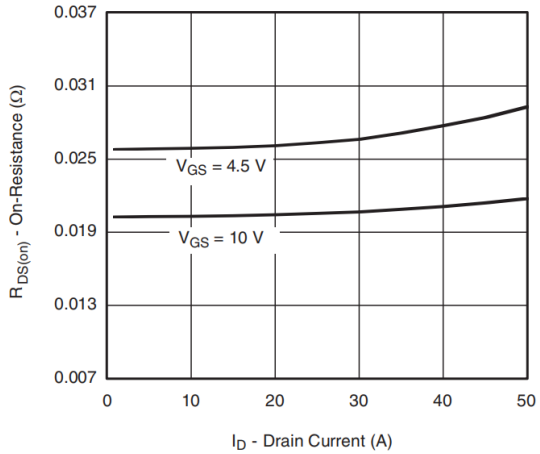
➢ Typical Performance Characteristics (T_A=25℃ unless otherwise noted)



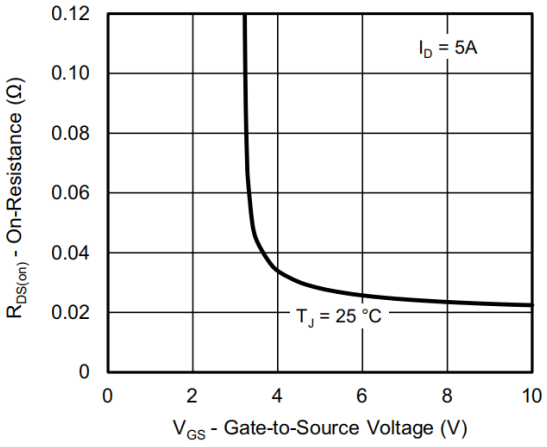
Output Characteristics



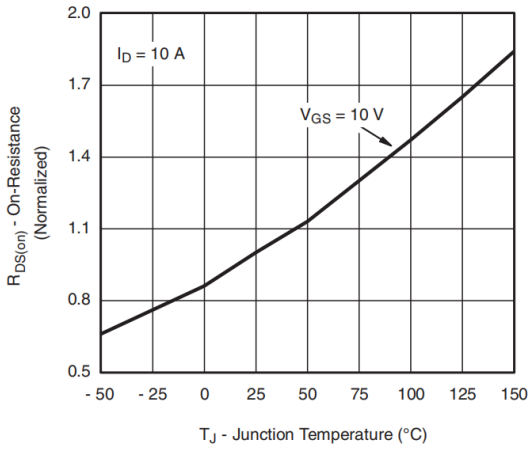
Transfer Characteristics



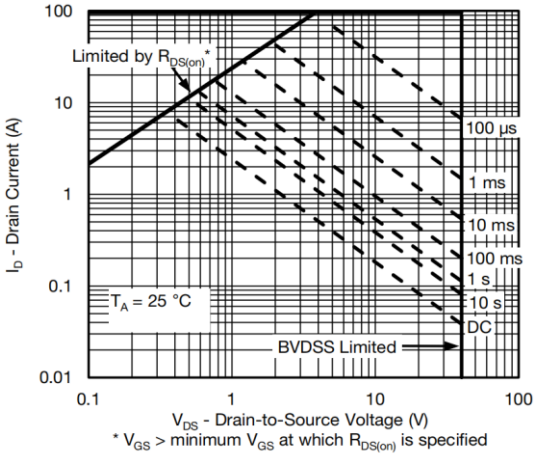
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Gate-to-Source Voltage

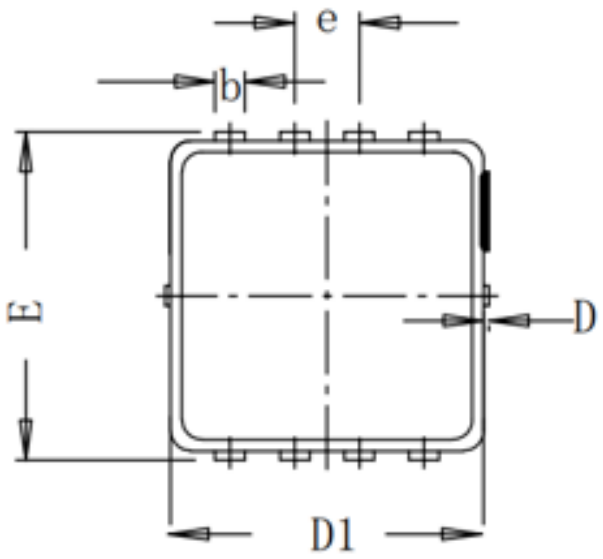


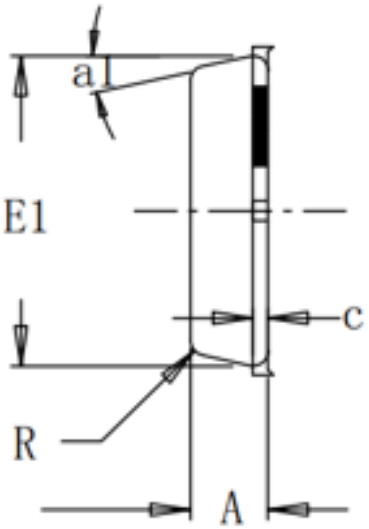
On-Resistance vs. Junction Temperature

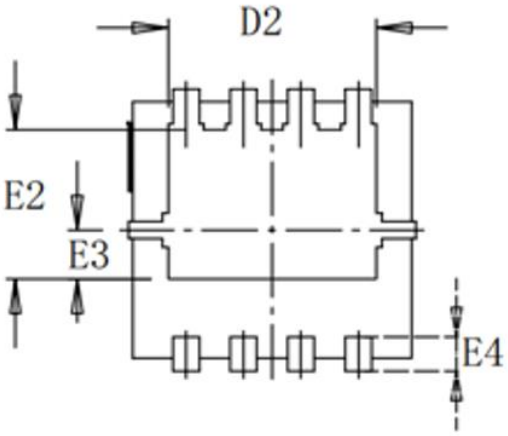


Safe Operating Area, Junction-to-Ambient

➢ Package Information







Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.75	0.78	0.81
b	0.297	0.3	0.35
c	-	0.152	-
D	0	0.05	0.1
D1	3.12	3.15	3.18
D2	-	2.35	-
E	3.2	3.3	3.4
E1	3.09	3.12	3.15
E2	-	1.75	-
E3	-	0.575	-
E4	-	0.4	-
R	-	0.15	-
e	0.65BSC		
a1°	-	12°	-

DISCLAIMER

SSCSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. SSCSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICIENCE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

THE GRAPHS PROVIDED IN THIS DOCUMENT ARE STATISTICAL SUMMARIES BASED ON A LIMITED NUMBER OF SAMPLES AND ARE PROVIDED FOR INFORMATIONAL PURPOSE ONLY. THE PERFORMANCE CHARACTERISTICS LISTED IN THEM ARE NOT TESTED OR GUARANTEED. IN SOME GRAPHS, THE DATA PRESENTED MAY BE OUTSIDE THE SPECIFIED OPERATING RANGE (E.G. OUTSIDE SPECIFIED POWER SUPPLY RANGE) AND THEREFORE OUTSIDE THE WARRANTED RANGE.

OUR PRODUCT SPECIFICATIONS ARE ONLY VALID IF OBTAINED THROUGH THE COMPANY'S OFFICIAL WEBSITE, CRM SYSTEM, OR OUR SALES PERSONNEL CHANNELS. IF CHANGES OR SPECIAL VERSIONS ARE INVOLVED, THEY MUST BE STAMPED WITH A QUALITY SEAL AND MARKED WITH A SPECIAL VERSION NUMBER TO BE VALID.